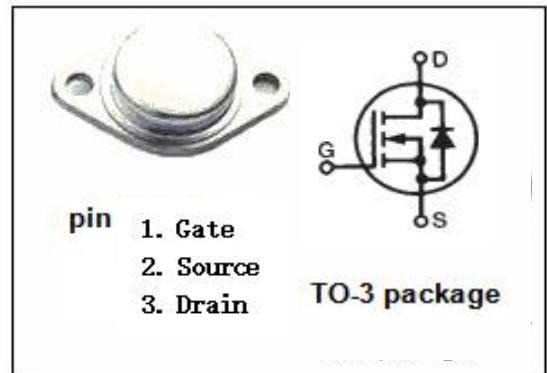


isc N-Channel MOSFET Transistor**IRF250****DESCRIPTION**

- Drain Current – $I_D=30A$ @ $T_c=25^\circ C$
- Drain Source Voltage-
 - : $V_{DSS}= 200V$ (Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.085 \Omega$ (Max)
- Nanosecond Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

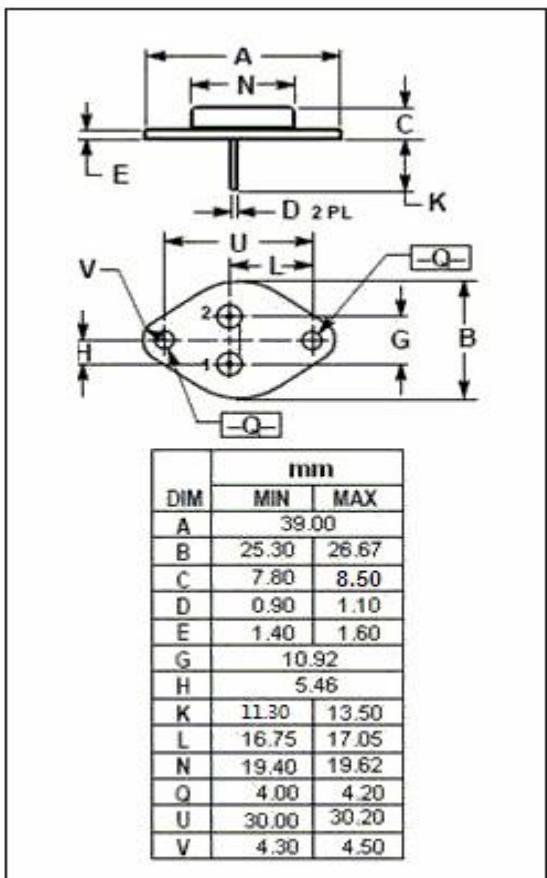
- Switching power supplies
- Switching converters,motor driver,relay driver

**ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_c=25^\circ C$	30	A
P_{tot}	Total Dissipation@ $T_c=25^\circ C$	150	W
T_j	Max. Operating Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	0.83	°C/W
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	30	°C/W



isc N-Channel MOSFET Transistor**IRF250****• ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0; I_D=250\mu\text{A}$	200			V
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}; I_D=250\mu\text{A}$	2		4	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-stage Resistance	$V_{\text{GS}}=10\text{V}; I_D=16\text{A}$			0.085	Ω
I_{GSS}	Gate Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}; V_{\text{DS}}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=200\text{V}; V_{\text{GS}}=0$			250	uA
V_{SD}	Diode Forward Voltage	$I_S=30\text{A}; V_{\text{GS}}=0$			2.0	V
C_{iss}	Input Capacitance	$V_{\text{DS}}=25\text{V}; V_{\text{GS}}=0\text{V}; f_T=1\text{MHz}$		2000	3000	pF
C_{rss}	Reverse Transfer Capacitance			300	500	
C_{oss}	Output Capacitance			800	1200	
t_r	Rise Time	$I_D=16\text{A}; V_{\text{DD}}=95\text{V}; R_L=4.7\Omega$			100	ns
$t_{\text{d}(\text{on})}$	Turn-on Delay Time				35	
t_f	Fall Time				100	
$t_{\text{d}(\text{off})}$	Turn-off Delay Time				125	

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